

## <<高频CMOS模拟集成电路基础>>

### 图书基本信息

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作者 : (土)莱布莱比吉

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### 内容概要

莱布莱比吉编著的《高频CMOS模拟集成电路基础（影印版）》以设计为核心理念从基础模拟电路讲到射频集成电路的研发。

系统地介绍了高频集成电路体系的构建与运行，重点讲解了晶体管级电路的工作体系，设备性能影响及伴随响应，以及时域和频域上的输入输出特性。

《高频CMOS模拟集成电路基础（影印版）》适合电子信息专业的高年级本科生及研究生作为RFCMOS电路设计相关课程的教材使用，也适合模拟电路及射频电路工程师作为参考使用。

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编辑推荐

- With a design-centric approach , this textbook bridges the gap between fundamental analog electronic circuit textbooks and more advanced RF IC design texts.
- The major issues that must be taken into account when combining analog and digital circuit building blocks are covered , together with the key criteria and parameters that are used to describe system-level performance.
- Simple circuit models enable a robust understanding of high-frequency design fundamentals , and SPICE simulations are used to check results and fine-tune the design.
- Analog integrated circuit designers and RF circuit designers in industry who need help making design choices will also find this a practical and valuable reference.

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